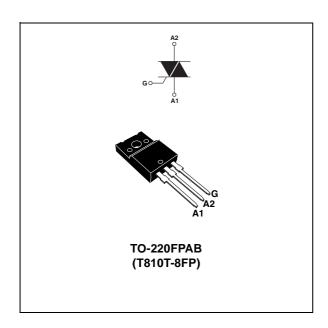


8 A logic level Triac

Datasheet - production data



Description

Available in through-hole full pack package, the T810T-8FP Triac can be used for the on/off or phase angle control function in general purpose AC switching. This device can be directly driven by a microcontroller due to its 10 mA gate current requirement.

Provides UL certified insulation rated at 1500 V rms.

Table 1. Device summary

Symbol	Value	Unit
I _{T(rms)}	8	Α
V_{DRM}, V_{RRM}	800	V
V_{DSM}, V_{RSM}	900	V
I _{GT}	10	mA

Features

- Medium current Triac
- Three quadrants
- ECOPACK[®]2 and RoHs compliant component
- Complies with UL standards (File ref: E81734)
- High performance Triac:
 - High T_i family
 - High dl/dt family
 - High dV/dt family

Applications

- · General purpose AC line load switching
- · Motor control circuits
- Small home appliances
- Lighting
- · Inrush current limiting circuits
- · Overvoltage crowbar protection

Characteristics T810T-8FP

1 Characteristics

Table 2. Absolute maximum ratings ($T_j = 25$ °C unless otherwise stated)

Symbol	Paramete	Value	Unit			
I _{T(rms)}	On-state rms current (full sine wave	T _c = 113°C	8	Α		
l	Non repetitive surge peak on-state	F = 50 Hz	t = 20 ms	60	Α	
I _{TSM}	current (full cycle, T _j initial = 25 °C)	F = 60 Hz	t = 16.7 ms	63	А	
l ² t	I ² t value for fusing, T _j initial = 25 °C		t _p = 10 ms	24	A ² s	
V _{DRM} ,	Repetitive surge peak off-state volta	ae.	T _j = 150 °C	600	V	
V_{RRM}	Trepetitive surge peak oil-state voita	T _j = 125 °C	800	V		
V _{DSM} , V _{RSM}	Non repetitive surge peak off-state v	t _p = 10 ms	900	V		
dI/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $t_r \le 100 \text{ ns}$		100	A/µs		
I _{GM}	Peak gate current	t _p = 20 μs	T _j = 150 °C	4	Α	
P _{G(AV)}	Average gate power dissipation	1	W			
T _{stg}	Storage junction temperature range	- 40 to + 150	Ç			
T _j	Operating junction temperature range	- 40 to + 150	9			
T_L	Maximum lead temperature for soldering during 10 s			260	°C	
V _{ins}	Insulation rms voltage, 1 minute		1500	V		

Table 3. Electrical characteristics ($T_j = 25$ °C, unless otherwise stated)

Symbol	Test conditions Quadrant			Value	Unit
I _{GT} ⁽¹⁾	$V_D = 12 \text{ V}, R_L = 30 \Omega$	1 - 11 - 111	Min.	0.5	mA
'GT`		1 - 11 - 111	Max.	10	
V _{GT}	$V_D = 12 \text{ V}, R_L = 30 \Omega$	1 - 11 - 111	Max.	1.3	V
V _{GD}	$V_D = V_{DRM}$, $R_L = 3.3 \text{ k}\ \Omega$, $T_j = 150\ ^{\circ}\text{C}$	1 - 11 - 111	Min.	0.2	V
I _H ⁽¹⁾	I _T = 500 mA		Max.	15	mA
	I _G = 1.2 I _{GT}	I - III	Max.	20	mA
IL		II	Max.	25	mA
dV/dt (1)	$V_D = V_R = 536 \text{ V, gate open}$	T _j = 125 °C	Min.	250	V/µs
dv/dt · /	$V_D = V_R = 402 \text{ V, gate open}$	T _j = 150 °C	IVIIII.	170	V/µs
(dl/dt)c (1)	(dV/dt)c = 0.1 V/µs	T _j = 125 °C	Min.	6.0	A/ms
(ul/ut)C · /		T _j = 150 °C	IVIIII.	4.2	
(dl/dt)c (1)	(dV/dt)c = 10 V/µs	T _j = 125 °C	Min.	3.2	- A/ms
(al/at)c ((αν/αι)ο – το ν/μο	T _j = 150 °C	IVIIII.	1.4	

^{1.} For both polarities of A2 referenced to A1

T810T-8FP Characteristics

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Symbol	Test conditions			Value	Unit
V _T ⁽¹⁾	I _{TM} = 11.3 A, t _p = 380 μs	T _j = 25 °C	Max.	1.55	V
V _{t0} (1)	Threshold voltage	T _j = 150 °C	Max.	0.85	V
R _d ⁽¹⁾	Dynamic resistance	T _j = 150 °C	Max.	57	mΩ
	V _{DRM} = V _{RRM} = 800 V	T _j = 25 °C	- Max.	5	μΑ
I _{DRM} I _{RRM}		T _j = 125 °C		0.8	mA
'KKIVI	V _{DRM} = V _{RRM} = 600 V	T _j = 150 °C	Max.	2.4	IIIA

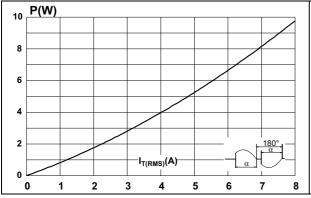
^{1.} For both polarities of A2 referenced to A1

Table 5. Thermal resistance

Symbol	Parameter	Value	Unit
R _{th(j-c)}	Junction to case (AC)	3.8	°C/W
R _{th(j-a)}	Junction to ambient (DC)	60	°C/W

Figure 1. Maximum power dissipation versus on-state rms current (full cycle)

Figure 2. On-state rms current versus case temperature (full cycle)



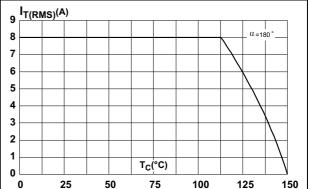
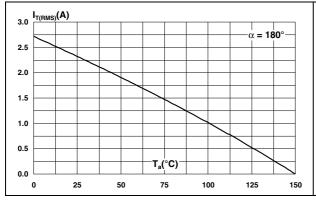
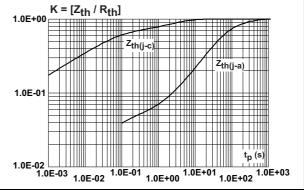


Figure 3. On-state rms current versus ambient temperature (free air convection)

Figure 4. Relative variation of thermal impedance versus pulse duration

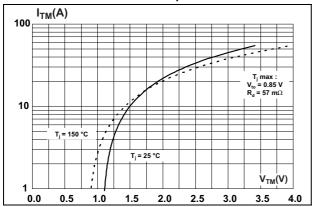




Characteristics T810T-8FP

Figure 5. On-state characteristics (maximum values)

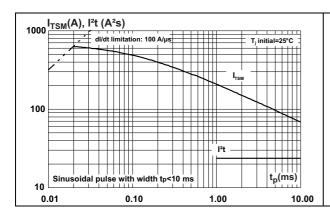
Figure 6. Surge peak on-state current versus number of cycles



 $I_{TSM}(A)$ 70 60 50 Non repetitive T_j initial=25°C 40 30 20 Repetitive 10 T_C= 113 °C Numbe 0 1 10 1000 100

Figure 7. Non repetitive surge peak on-state current and corresponding values of I²t

Figure 8. Relative variation of gate trigger current and gate voltage versus junction temperature (typical values)



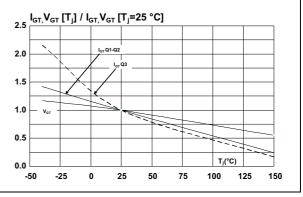
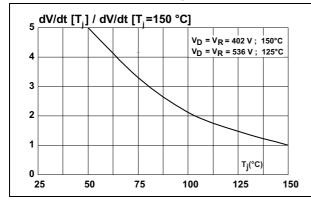
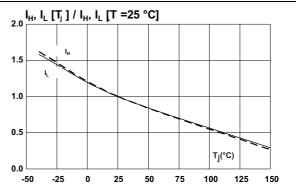


Figure 9. Relative variation of static dV/dt immunity versus junction temperature (typical values)

Figure 10. Relative variation of holding and latching current versus junction temperature (typical values)

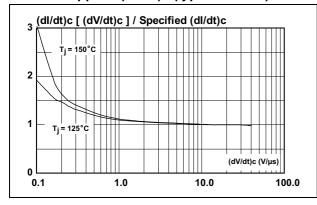




T810T-8FP Characteristics

Figure 11. Relative variation of critical rate of decrease of main current (di/dt)c versus reapplied (dV/dt)c (typical values)

Figure 12. Relative variation of critical rate of decrease of main current (di/dt)c versus junction temperature (typical values)



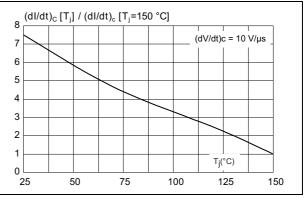
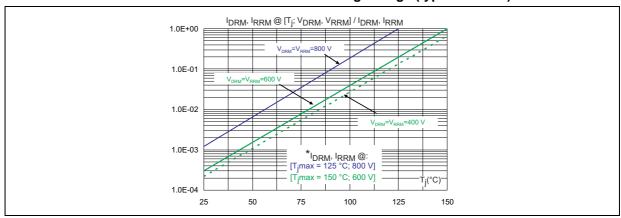


Figure 13. Relative variation of leakage current versus junction temperature for different values of blocking voltage (typical values)



Package information T810T-8FP

2 Package information

- Epoxy meets UL94, V0
- Lead-free package
- Recommended torque: 0.4 to 0.6 N·m

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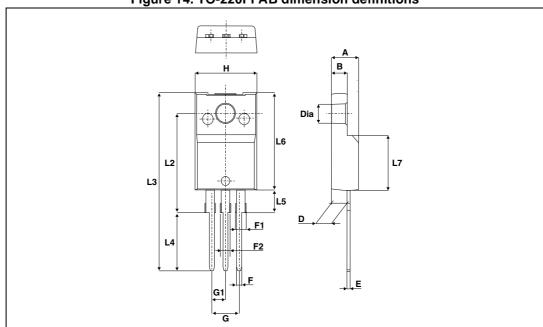


Figure 14. TO-220FPAB dimension definitions

Table 6. TO-220FPAB dimension values

	Dimensions					
Ref.	Millim	neters	Inches			
	Min.	Max.	Min.	Max.		
А	4.4	4.6	0.173	0.181		
В	2.5	2.7	0.098	0.106		
D	2.5	2.75	0.098	0.108		
E	0.45	0.70	0.018	0.027		
F	0.75	1	0.030	0.039		
F1	1.15	1.70	0.045	0.067		
F2	1.15	1.70	0.045	0.067		
G	4.95	5.20	0.195	0.205		
G1	2.4	2.7	0.094	0.106		
Н	10	10.4	0.393	0.409		
L2	16 ⁻	Тур.	0.63	Тур.		
L3	28.6	30.6	1.126	1.205		
L4	9.8	10.6	0.386	0.417		
L5	2.9	3.6	0.114	0.142		
L6	15.9	16.4	0.626	0.646		
L7	9.00	9.30	0.354	0.366		
Dia.	3.00	3.20	0.118	0.126		

Ordering information T810T-8FP

3 Ordering information

Figure 15. Ordering information scheme

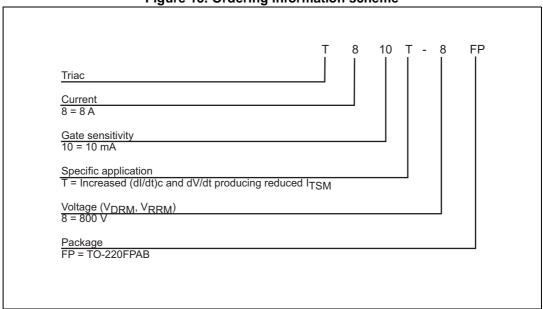


Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
T810T-8FP	T810T-8FP	TO-220FPAB	2.0 g	50	Tube

4 Revision history

Table 8. Document revision history

Date	Revision	Changes
05-Feb-2014	1	Initial release.

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